Approved	Checked	Designed	DEVELOPMENT SPECIFICATION Tentative P/N:LNJ210C62RA				
		K. Ishitsuka					

T Y P E	Red Emitting Diode					
APPLICATION	Indicators					
MATERIAL	InGaAlP					
OUTLINE	Attached					
ABSOLUTE MAXIMUM RATINGS	P	*1 I_{FP}	I_{FDC}	V_R	Topr	Tstg
	55 mW	60 mA	20 mA	4 V	-25～+85 ℃	-30～+100 ℃
CONDITION	Ta=25±3 ℃					

Test Specification

Item	Symbol	Condition	Typ.	Limit		Unit
				Min	Max	
Forward Voltage	V_F	I_F=10 mA	1.92		2.5	V
Reverse Leakage Current	I_R	V_R= 4 V		12	100	μA
Luminous Intensity *2	I_O	I_F=10 mA DC	23	12		mcd
Peak Emission Wavelength	λp	I_F=10 mA DC	645			nm
Spectral Line Half Width	Δλ	I_F=10 mA DC	15			nm

*1 · The Condition of I_{FP} is duty 10 %, Pulse width 1 ms
· Please contact the Panasonic local office if you design at low current (below 1 mA DC) or pulse current operation and have any questions.

*2 Measurement Tolerance is ±20%.

NOTE

★1. Terminal:Plated with gold on copper base.

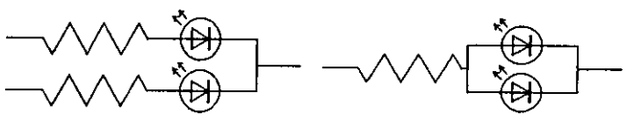
★2. Beware of destruction by static electricity in handling the LED.

★3. Package : Clear type.

★4. Soldering conditions.
Refer to Handling note.

★5. Care should be taken that soldering is done within 3-days after opening the dry package and reel.

★6. Circuit to operate LED.



(A) (B)

(A) Recommended circuit.
(B) The difference of brightness between the LED could be found due to the V_F characteristics of each LED.

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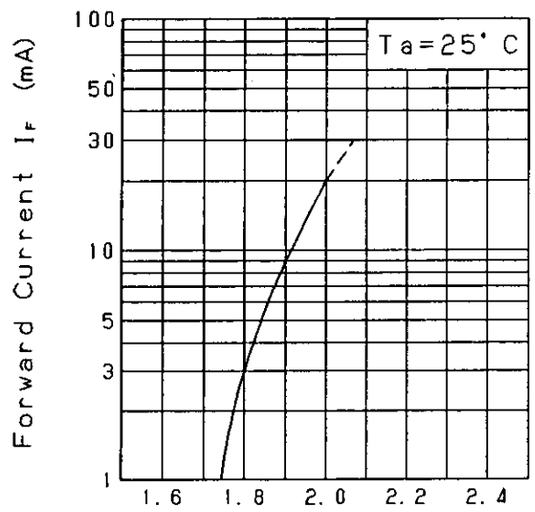
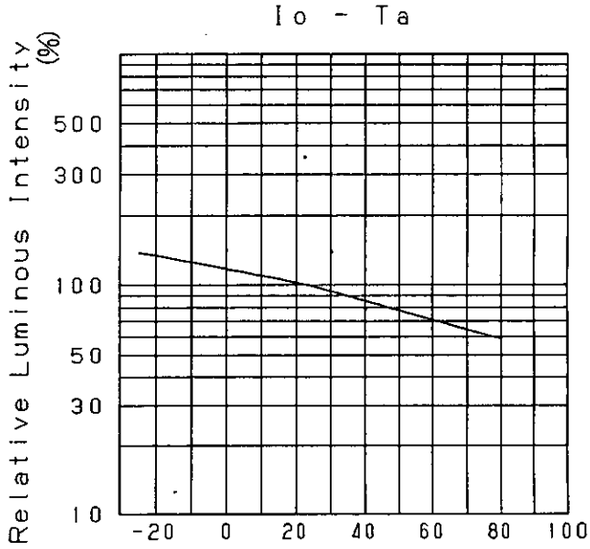
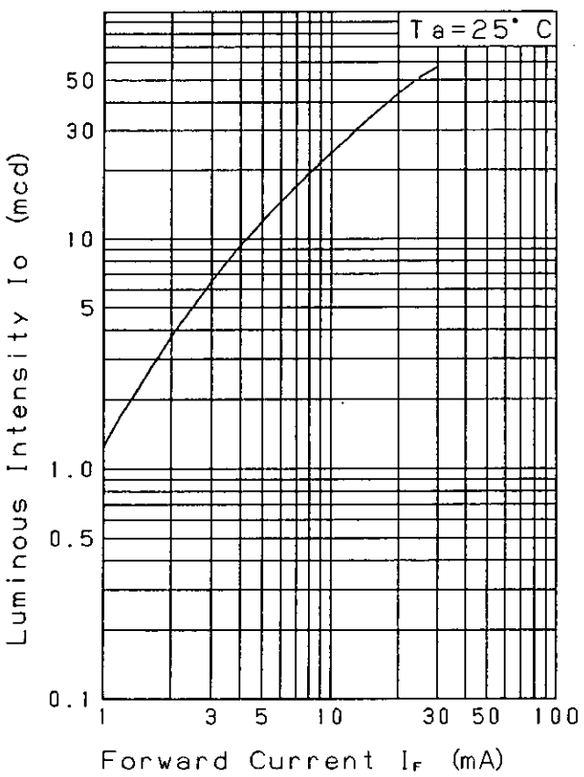
I_F - V_F



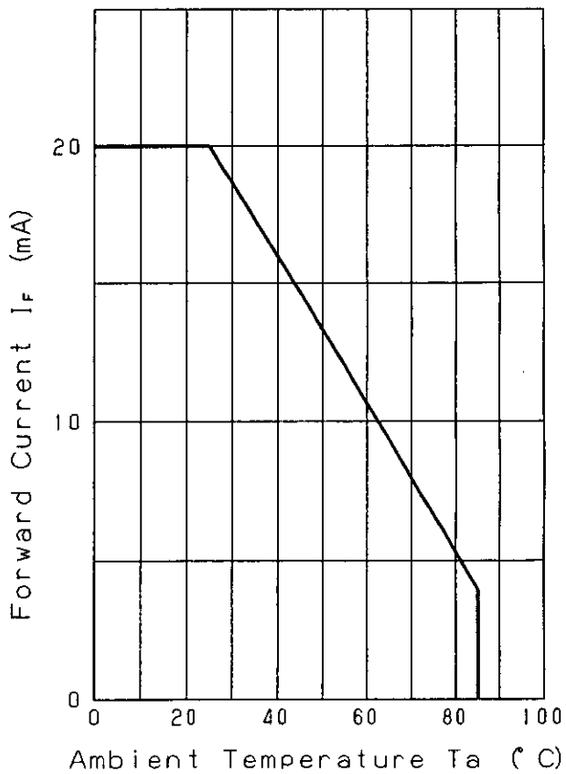
Io - Ta



Io - I_F



I_F - Ta



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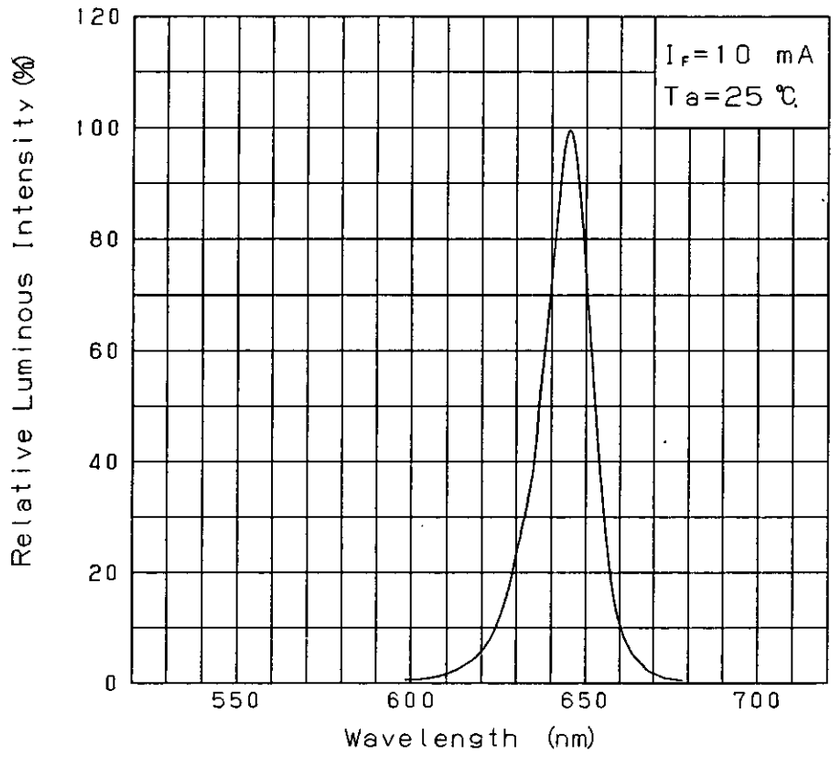
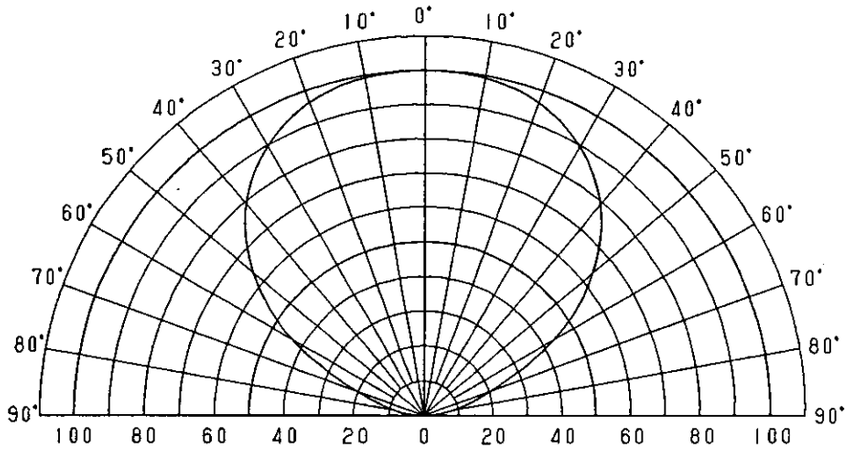
Relative Luminous Intensity Wavelength Characteristics



Directive Characteristics



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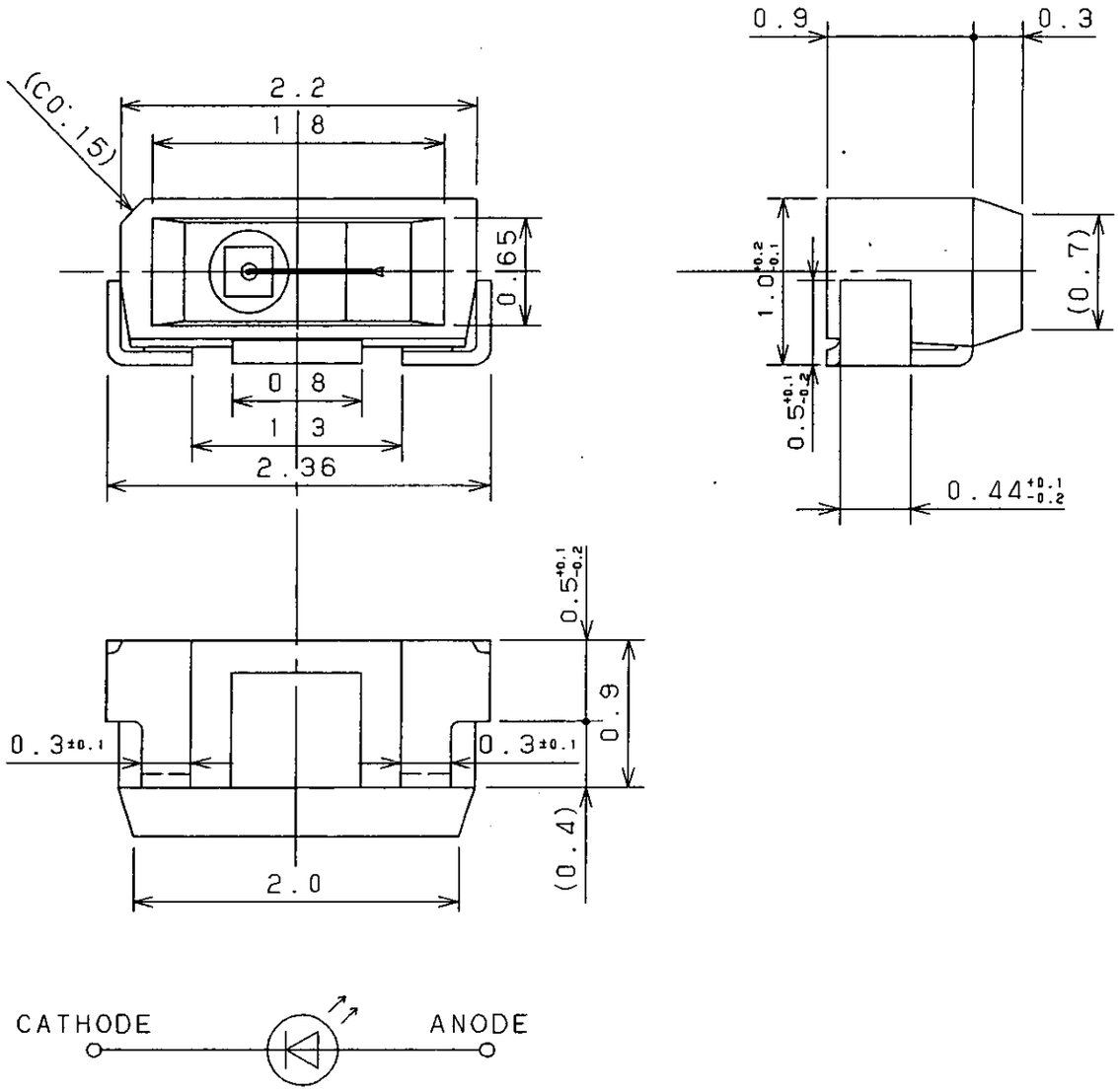
DEVELOPMENT SPECIFICATION
(OUTLINE) Tentative
P/N:LNJ210C62RA



(NOTE)
1.Unit:mm
2.Tolerance unless specified is ±0.15.

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